

Form PTO-1449		Docket Number 204552018400	Application Number 09/598,384
INFORMATION DISCLOSURE CITATION IN AN APPLICATION <i>(Use several sheets if necessary)</i>		Applicant	
		Yasuaki HIRANO	
		Filing Date June 21, 2000	Group Art Unit to be assigned
		Mailing Date October 4, 2000	2818

U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO
TP	1.	6/20/97	9-162373	JP	—	—	abstract only

OTHER DOCUMENTS

(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
TP	2.	Kato et al., "AND cell structure for a 3V-only 64 Mbit Flash Memory", Technical Report of IEICE, ICD93-128, p. 37, 1993
TP	3.	Onoda et al., "A novel cell structure suitable for a 3 volt operation, sector erase flash memory", Technical Report of IEICE, ICD93-26, p. 15, 1993
TP	4.	Kim et al., "A novel dual string NOR (DuSNOR) memory cell technology scalable to the 256 Mbit and 1 Gbit flash memories", IEDM 95-263, pp. 11.1.1-4, 1995
TP	5.	Yamauchi et al., "A new cell structure for sub-quarter micron high density flash memory", IEDM 95-267, PP. 11.2.1-4, 1995
TP	6.	Hirano et al., "A sensing scheme for a ACT flash memory", Technical Report of IEICE, ICD97-21, pp. 37-42, 1997

EXAMINER: Trong Phan

DATE CONSIDERED: 12/19/01

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